Coherent, Monochromatic EUV Beams for Characterization and Defect Inspection of Lithography Masks

The next generation of high resolution EUV lithography require tools for reliable characterization and defect inspection of lithography masks. Ideally the inspection is used with the same type of radiation and wavelength used in the lithography process. Researchers from the PSI in Switzerland demonstrate use of coherent, monchromatic EUV beams at 13.5nm to perform coherent diffraction imaging or lithography masks for defect inspection. New, more advanced image processing algorithms are applied to the image data taken with a large size, in vacuum CCD camera.

Featured Paper/Publication: Beam drift and partial probe coherence effects in EUV reflective-mode coherent diffractive imaging, Optics Express, 2018

Reference Lab: Patrick Helfenstein, Yasin Ekinci et al, PSI, Switzerland

Featured Product: MTE